SOI WAFERS - SPECIFICATION SOI-380-2-100

Overall wafer
Growth method: CZ
Bonding method: Fusion bonding
Diameter: 100 ± 0.5mm
Primary Flat Orientation: {110} ± 0.5°
Primary Flat Length: 32.5 ± 2.5 mm
Non-SOI edge area: < 1.5mm (preferably 0mm if not affecting quality)
Edge Profile: Rounded

Device Layer
Type / Dopant: P / Boron
Orientation incl. off-orientation: {100} ± 0.5°
Resistivity: 1 – 10 Ohmcm
Thickness: 100 ± 0.7μm

Buried Oxide
Oxide Thickness: 2.00μm ± 3%

Handle Wafer
Type / Dopant: P / Boron
Orientation incl. off-orientation: {100} ± 0.5°
Resistivity: 1 – 10 Ohmcm
Thickness: 380 ± 5μm
Back Surface: Polished, without remaining oxide on backside
Laser Marking: Wafers backside according to PO